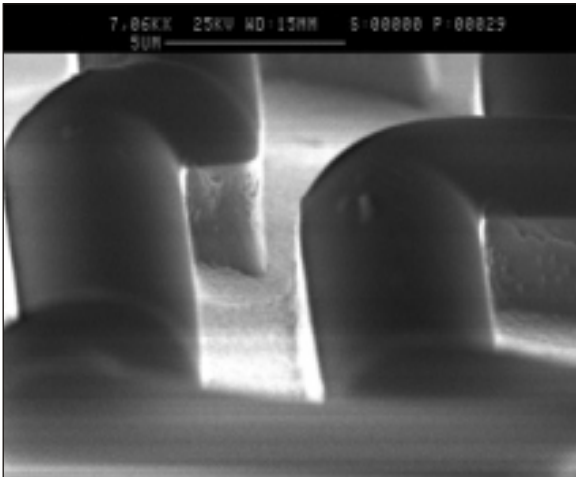
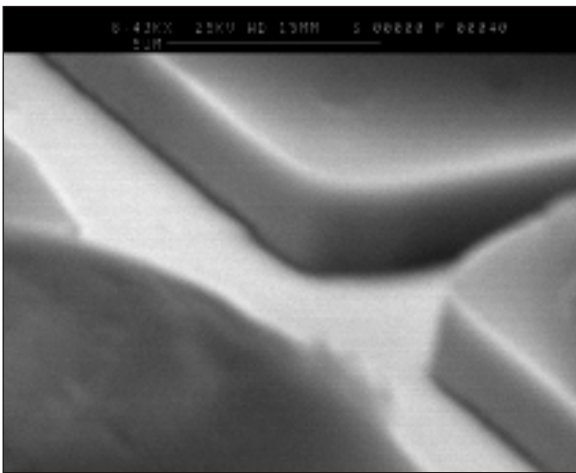


# Plasmalab Data

## HgCdTe (CMT) Low Energy ICP Etching



4 µm deep low bias etches in HgCdTe



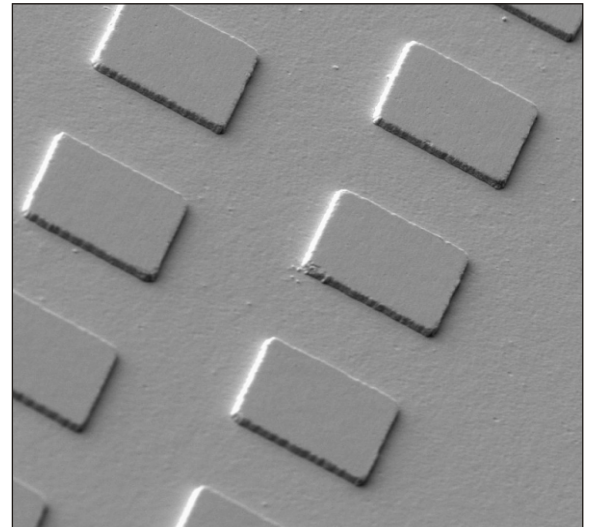
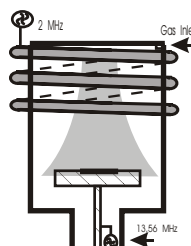
*Plasmalab System 100*  
*Plasmalab System 133*  
*Plasmalab 80 Plus*

**Technology:**

Inductive Coupled Plasma Etch  
 Very efficient substrate cooling

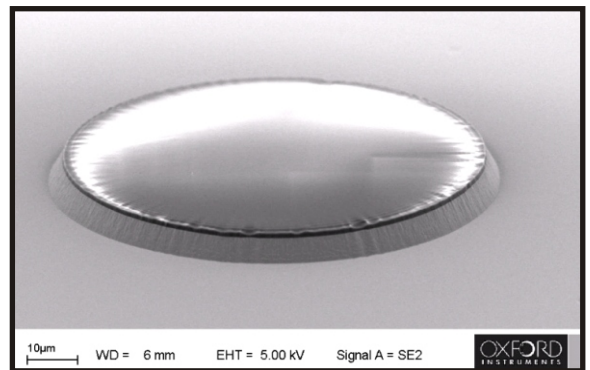
**Results:**

- rate 0.05 to 0.5 µ/ min
- very low bias / damage process
- selectivity > 10:1 to resist
- > 20:1 to SiO<sub>2</sub> or SiN<sub>x</sub>
- uniformity < +/- 4% (50mm diameter)
- excellent profile control



SEM MAG: 1.12 kx DET: SE Detector HV: 15.0 kV DATE: 08/26/04 PC: 5 Scan speed: 6 50 µm Vega ©Tescan Digital Microscopy Imaging

50 µm wide structures in CMT  
 Courtesy of SITP China



OPT lab: 8 µm deep CMT etch,  
 PR mask still in place, controllable profile

